P-Channel Enhancement Mode MOSFET

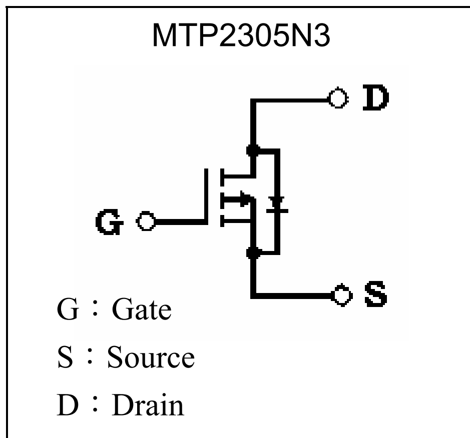
MTP2305N3

BV_{DSS}	-20V
I_D	-4.3A
R_{DSON}@V_{GS}=-4.5V, I_D=-4.2A	52mΩ (typ.)
R_{DSON}@V_{GS}=-2.5V, I_D=-2A	66mΩ (typ.)
R_{DSON}@V_{GS}=-1.8V, I_D=-1A	79mΩ (typ.)

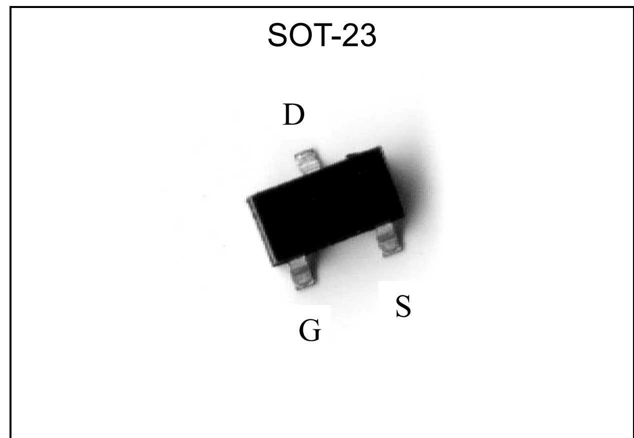
Features

- Advanced trench process technology
- Super high density cell design for extremely low on resistance
- Reliable and rugged
- Compact and low profile SOT-23 package
- Pb-free lead plating and halogen-free package

Equivalent Circuit

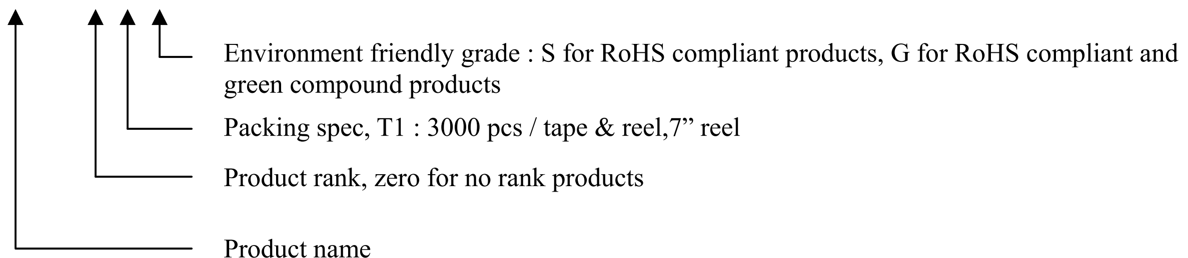


Outline



Ordering Information

Device	Package	Shipping
MTP2305N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current @T_A=25°C, V_{GS}=-4.5V (Note 1)	I_D	-4.3	A
Continuous Drain Current @T_A=70°C, V_{GS}=-4.5V (Note 1)	I_D	-3.4	A
Pulsed Drain Current (Note 2)	I_{DM}	-20	A
Maximum Power Dissipation (Note 1)	P_D	1.38	W
Linear Derating Factor		0.01	W/°C
Operating Junction and Storage Temperature	Tj, Tstg	-55~+150	°C

Note : 1. Surface mounted on 1 in² copper pad of FR-4 board, t≤5s; 270°C/W when mounted on minimum copper pad.
2. Pulse width limited by maximum junction temperature.

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient, max (Note)	$R_{\theta JA}$	90	°C/W
Thermal Resistance, Junction-to-Case, max	$R_{\theta JC}$	75	°C/W

Note : Surface mounted on 1 in² copper pad of FR-4 board, t≤5s ; 270°C/W when mounted on minimum copper pad.

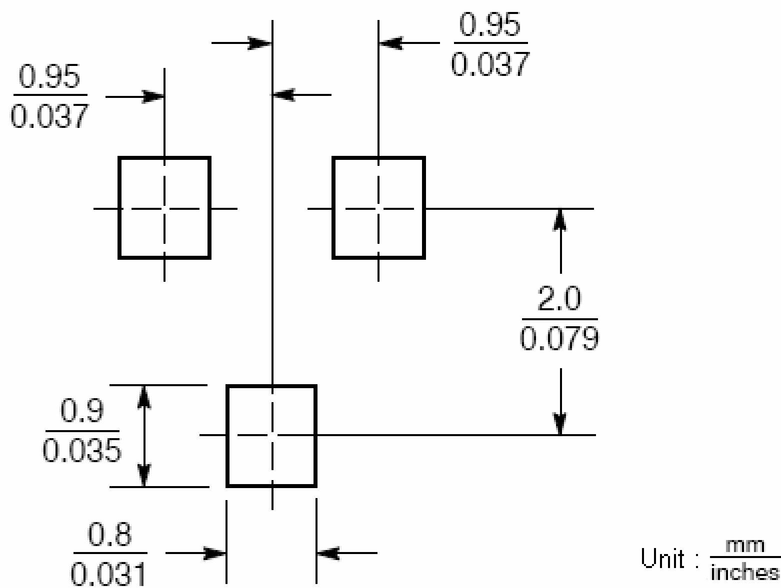
Electrical Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-20	-	-	V	V_{GS}=0, I_D=-250μA
$\Delta BV_{DSS}/\Delta Tj$	-	-0.02	-	V/°C	Reference to 25°C, I_D=-1mA
$V_{GS(th)}$	-0.5	-0.65	-	V	V_{DS}=V_{GS}, I_D=-250μA
I_{GSS}	-	-	±100	nA	V_{GS}=±12V, V_{DS}=0
I_{DSS}	-	-	-1	μA	V_{DS}=-20V, V_{GS}=0
	-	-	-10		V_{DS}=-16V, V_{GS}=0, Tj=70°C
*$R_{DS(ON)}$	-	44	53	mΩ	I_D=-4.5A, V_{GS}=-10V
	-	52	65		I_D=-4.2A, V_{GS}=-4.5V
	-	66	85		I_D=-2.0A, V_{GS}=-2.5V
	-	79	120		I_D=-1.0A, V_{GS}=-1.8V
*G_{FS}	-	8.3	-	S	V_{DS}=-5V, I_D=-2.8A
Dynamic					
Ciss	-	1101	-	pF	V_{DS}=-15V, V_{GS}=0, f=1MHz
Coss	-	69	-		
Crss	-	60	-		
*$t_{d(ON)}$	-	7	-	ns	V_{DS}=-15V, I_D=-4.3A, V_{GS}=-10V, R_D=3.6Ω, R_G=6Ω
*t_r	-	5	-		
*$t_{d(OFF)}$	-	38	-		
*t_f	-	9	-		

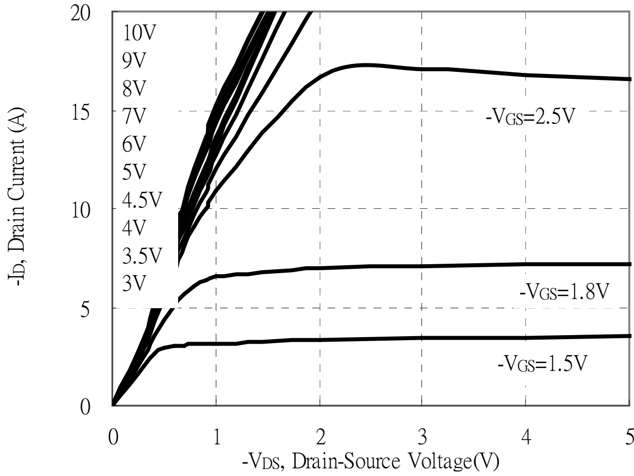
*Qg	-	10.6	-	nC	V_{DS}=-16V, I_D=-4.3A, V_{GS}=-4.5V,
*Qgs	-	2	-		
*Qgd	-	2.8	-		
Source-Drain Diode					
*V_{SD}	-	-0.78	-1.2	V	V_{GS}=0V, I_{SD}=-1.2A
*trr	-	28	-	ns	I_S=-4.3A, V_{GS}=0V, dI/dt=100A/µs
*Qrr	-	22	-	nC	

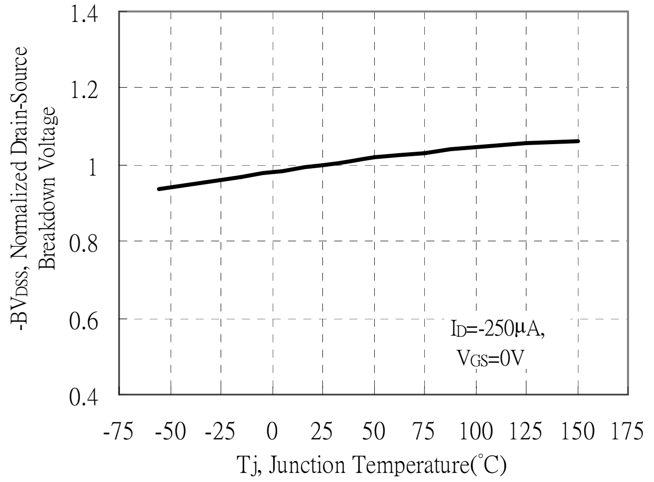
*Pulse Test : Pulse Width ≤300µs, Duty Cycle≤2%

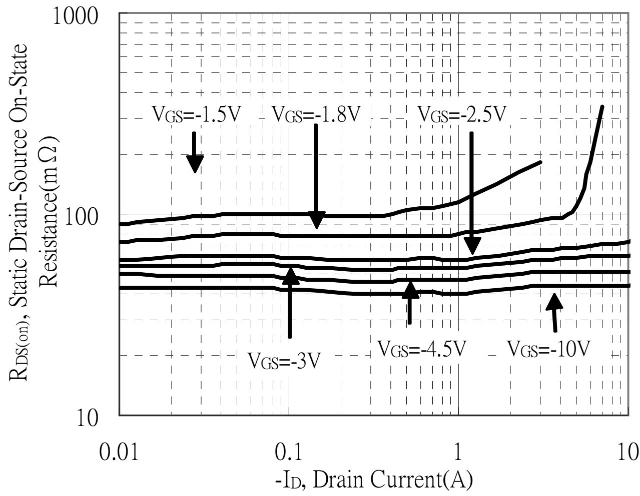
Recommended Soldering Footprint

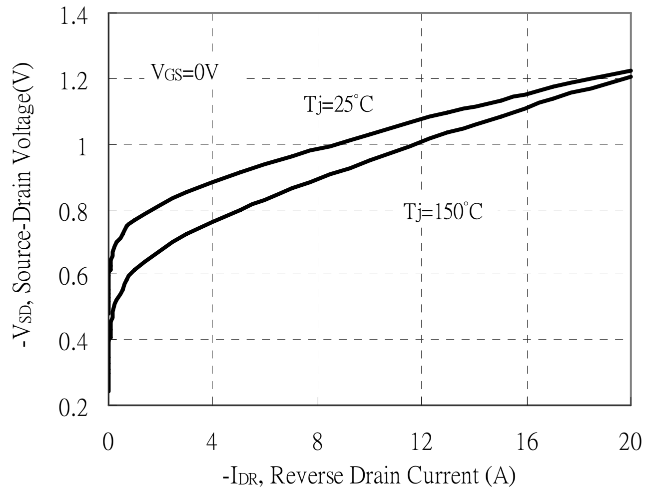


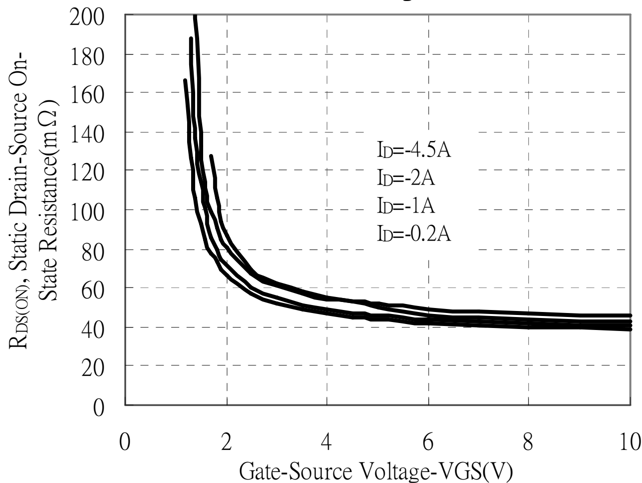
Typical Characteristics

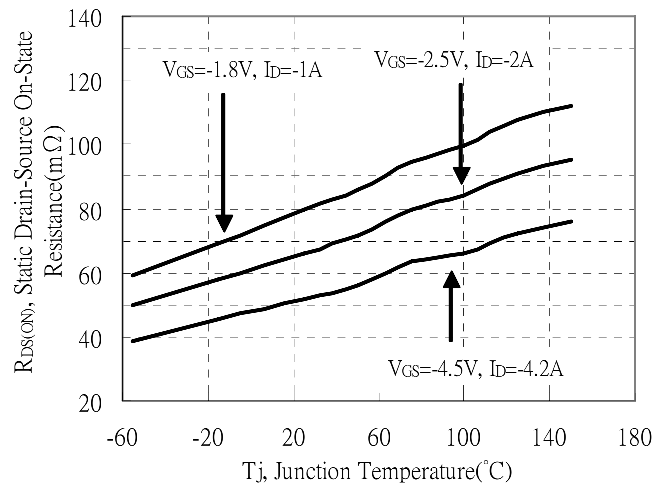




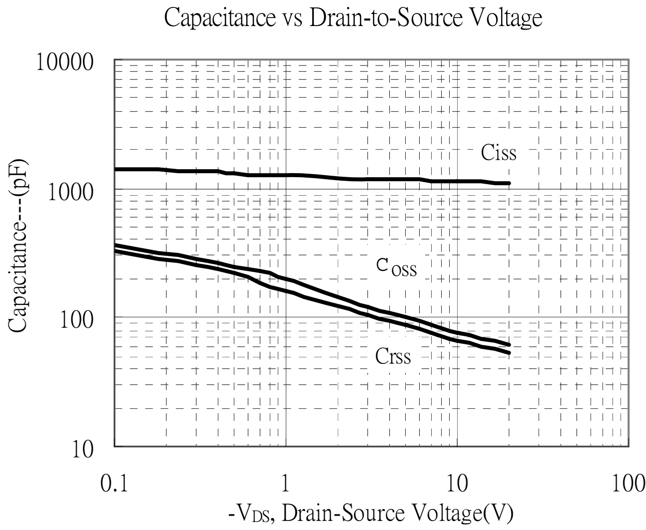


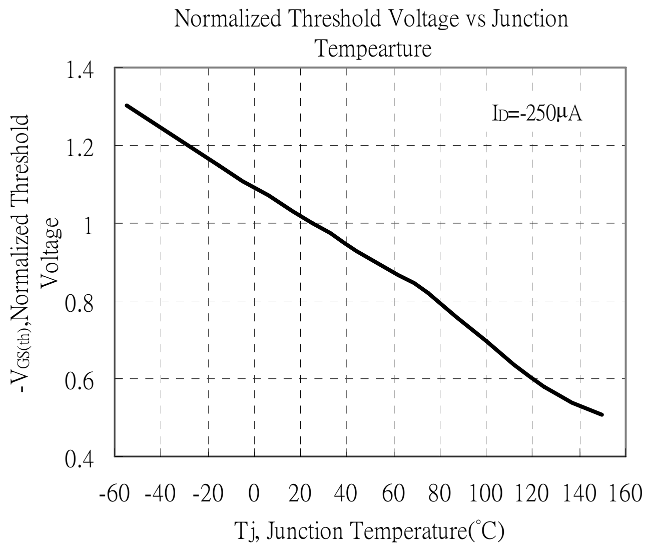


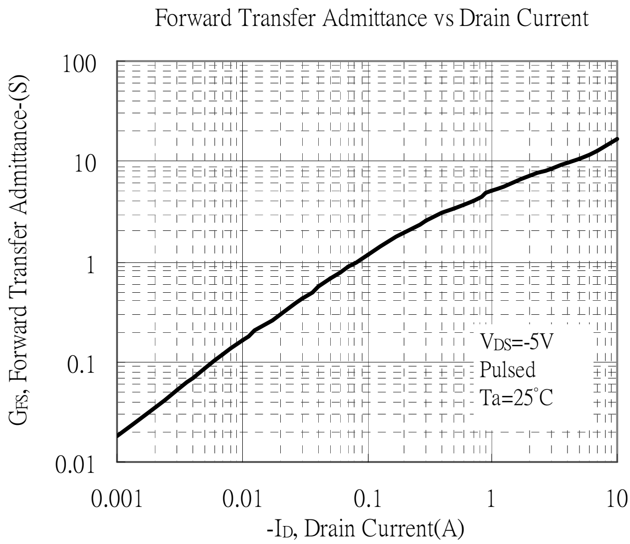


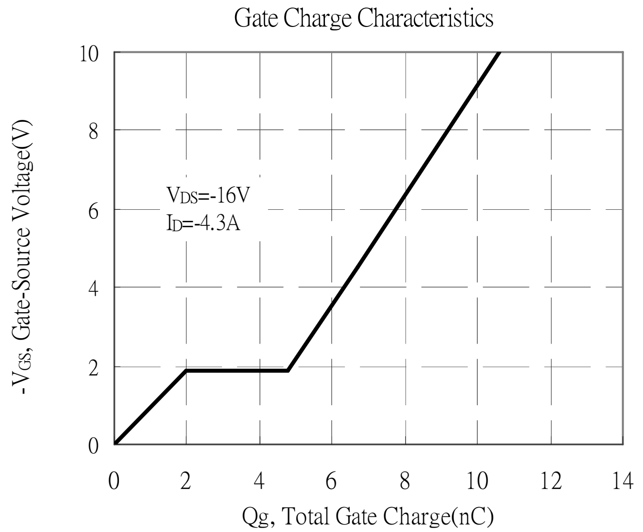


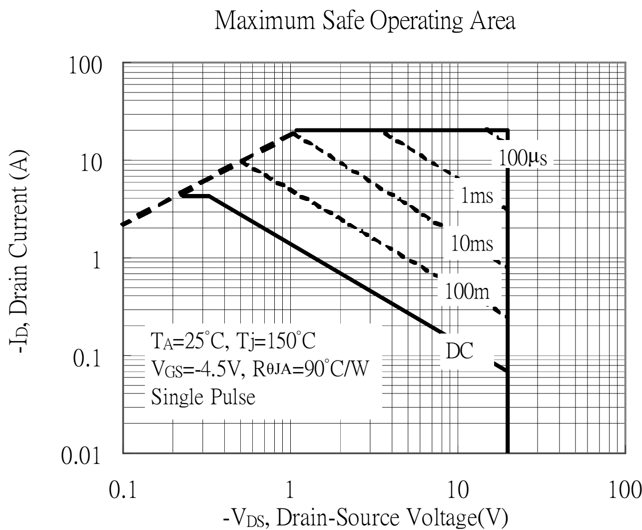
Typical Characteristics(Cont.)

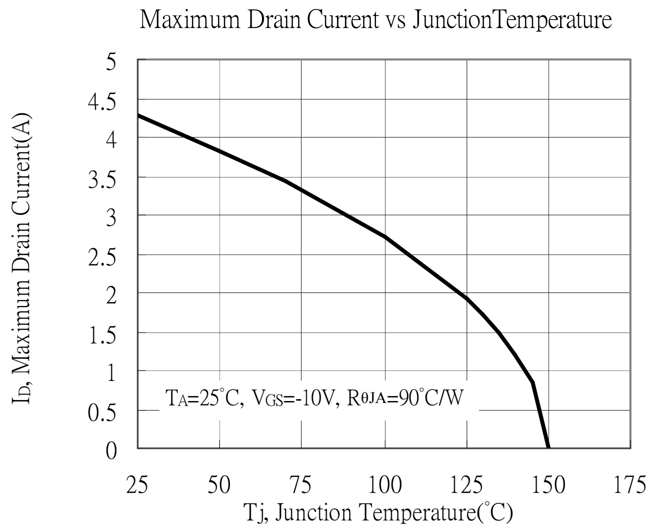












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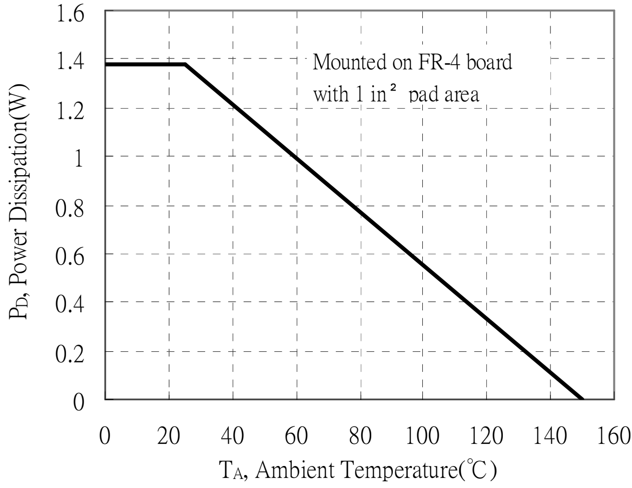
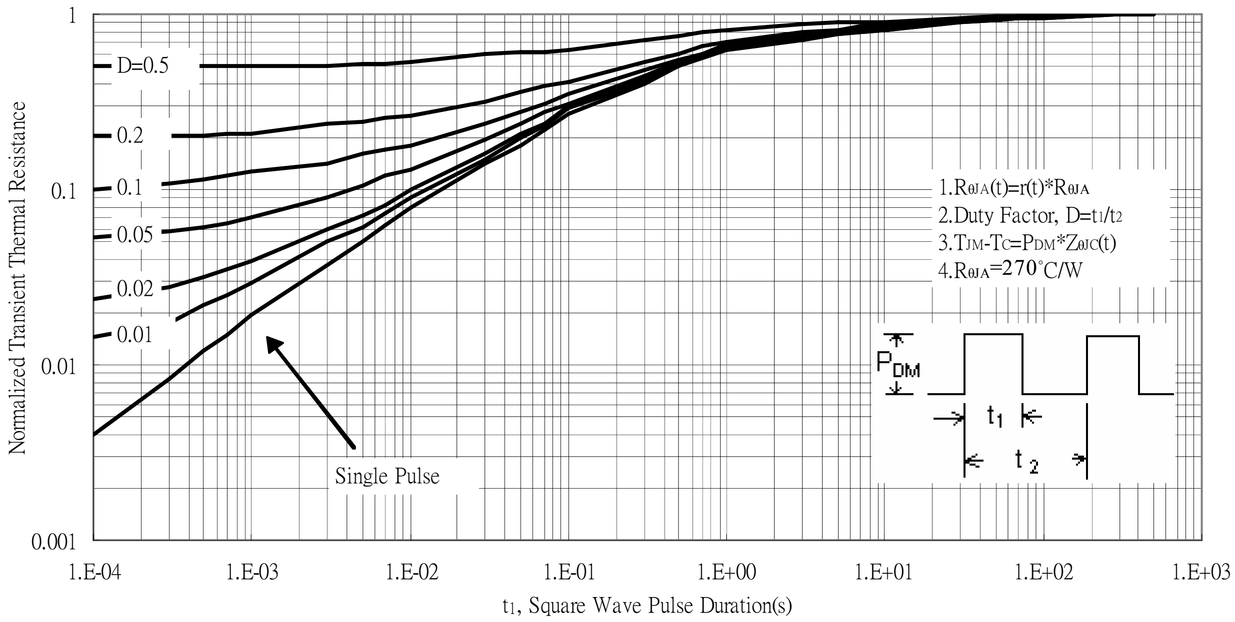
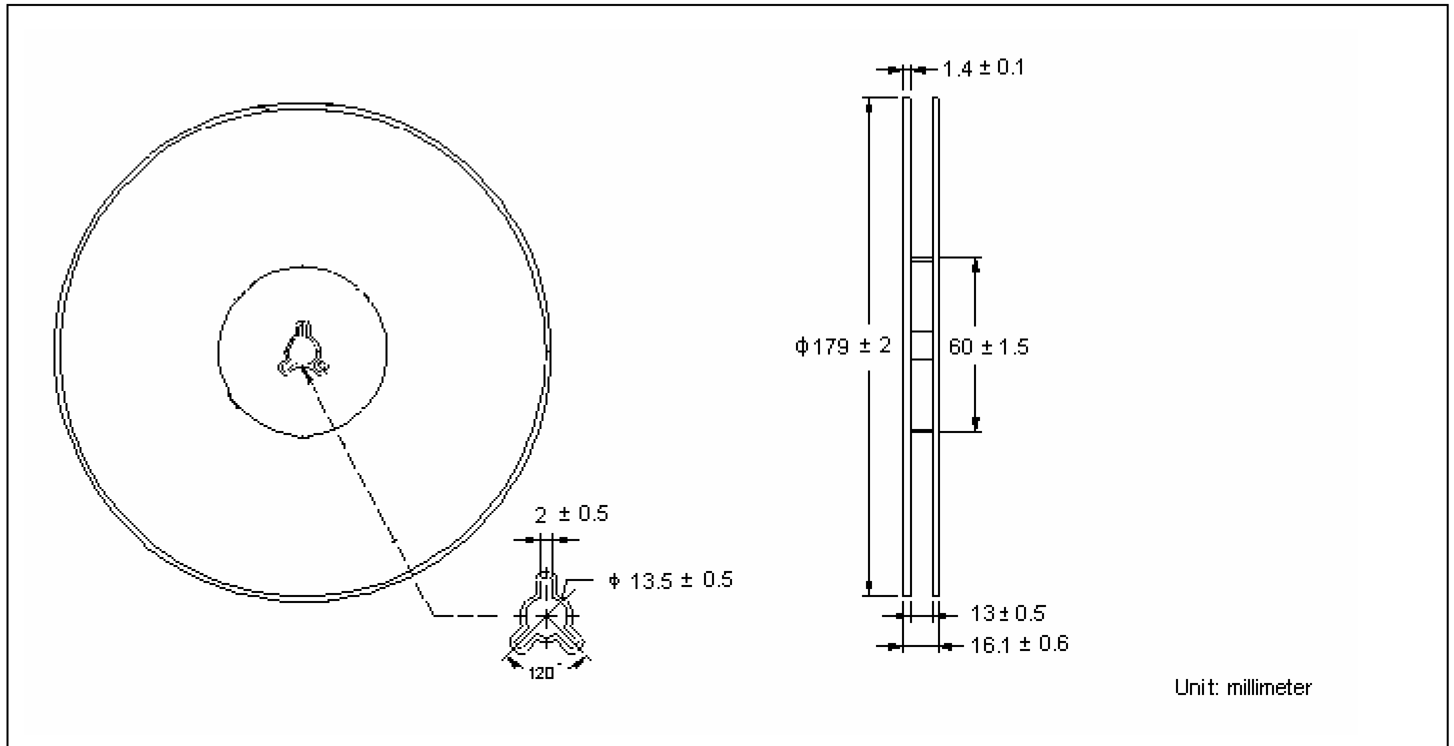




Reel Dimension



Carrier Tape Dimension

0.22±0.02
B
1.5+0.1/-0
B
2±0.05
See Note6
4.0±0.1
See Note1
A
1.75±0.1
0.6
3.5±0.05
See Note5
Bo
Ao
4.0±0.1
8+0.3/-0.1
1.0±0.1
A
0.2 Max
Ko
Section A-A
Section B-B

Ao=3.10±0.15
Bo=2.78±0.12
Ko=1.22±0.1

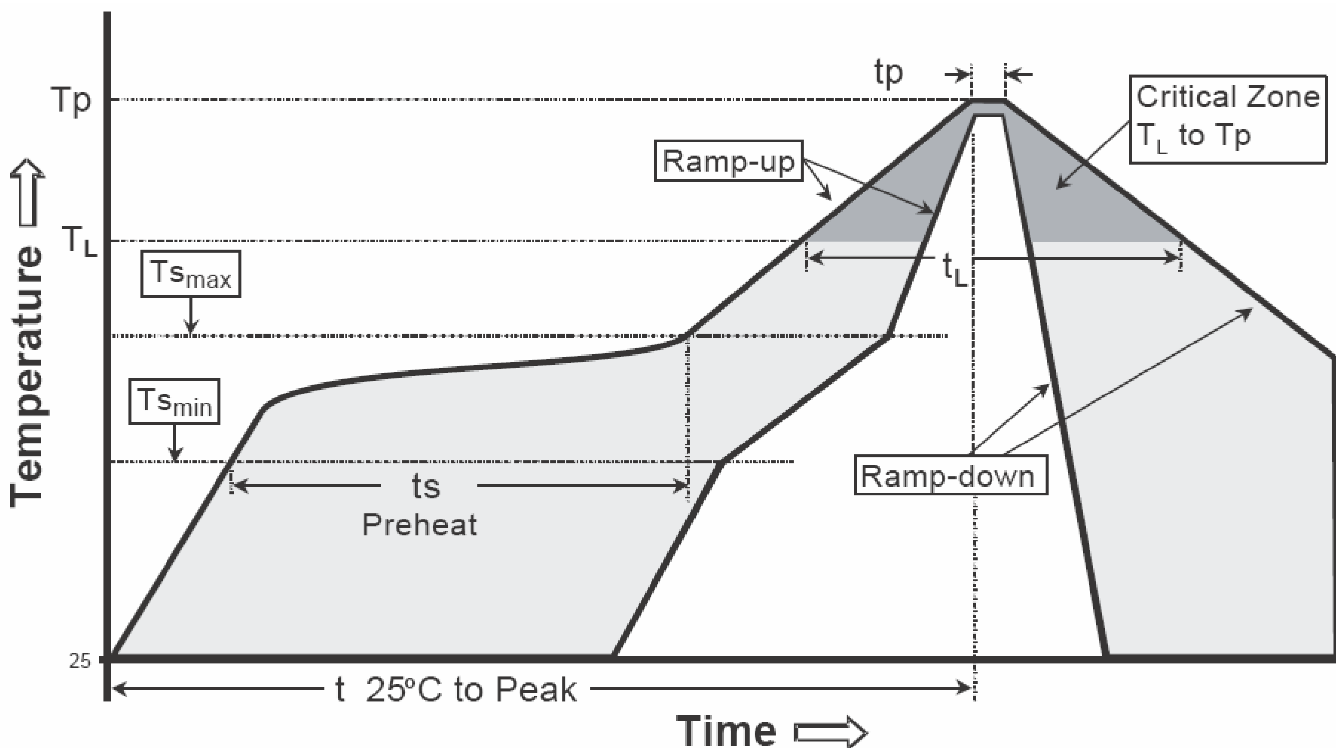
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

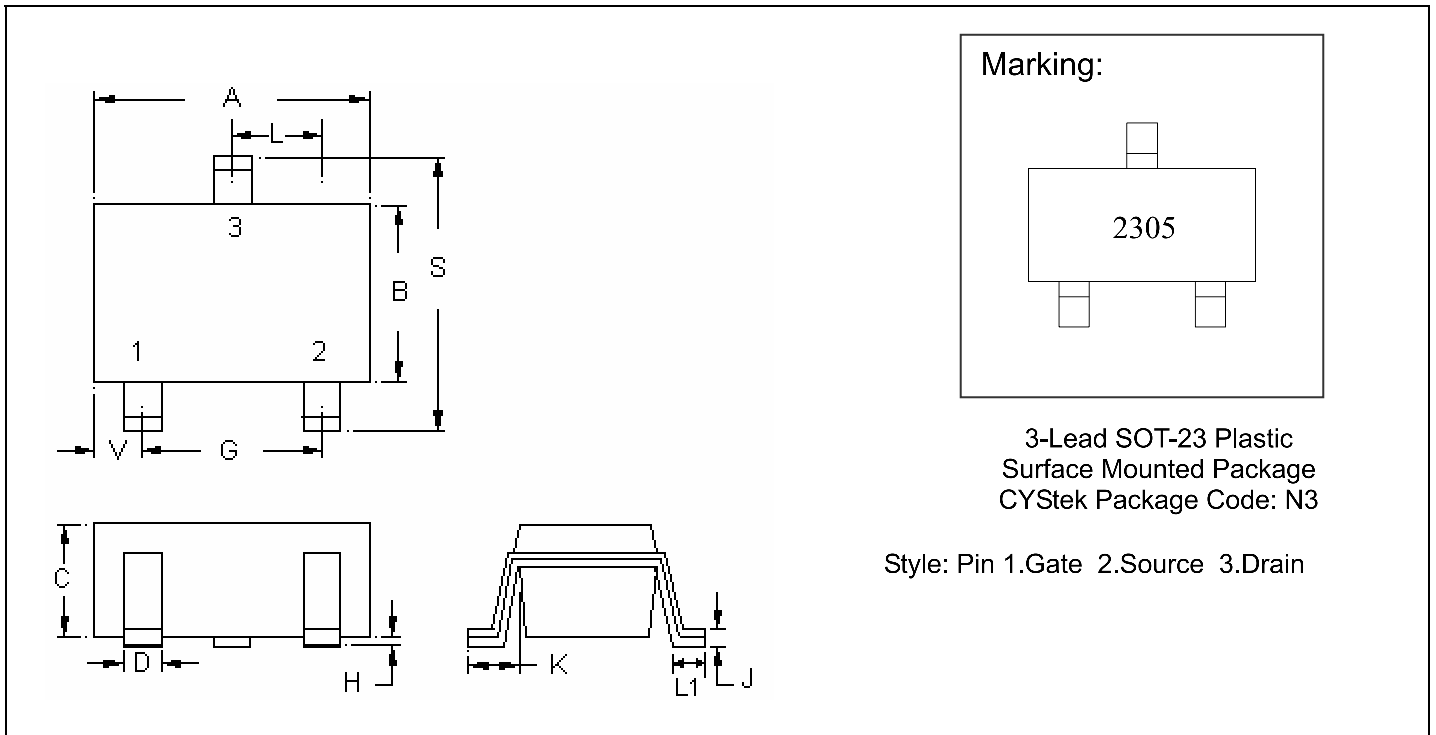
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(Ts min) −Temperature Max(Ts max) −Time(ts min to ts max)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



3-Lead SOT-23 Plastic
Surface Mounted Package
CYStek Package Code: N3

Style: Pin 1.Gate 2.Source 3.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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